

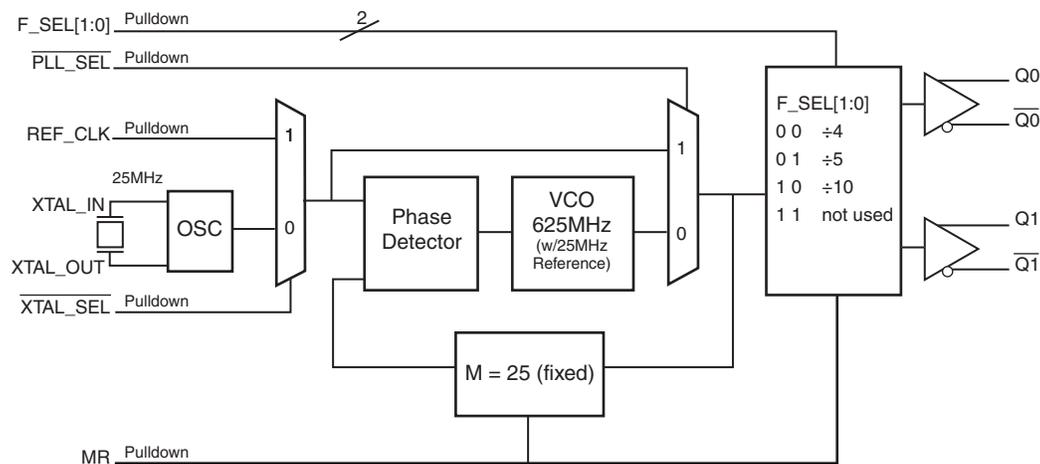
General Description

The 844002I-01 is a 2 output LVDS Synthesizer optimized to generate Ethernet reference clock frequencies. Using a 25MHz, 18pF parallel resonant crystal, the following frequencies can be generated based on the 2 frequency select pins (F_SEL[1:0]): 156.25MHz, 125MHz and 62.5MHz. The 844002I-01 uses IDT's 3rd generation low phase noise VCO technology and can achieve <1ps typical rms phase jitter, easily meeting Ethernet jitter requirements. The 844002I-01 is packaged in a small 20-pin TSSOP package.

Features

- Two differential LVDS outputs
- Selectable crystal oscillator interface or single-ended LVC MOS/LVTTL input
- Supports the following output frequencies: 156.25MHz, 125MHz, 62.5MHz
- VCO range: 560MHz – 680MHz
- RMS phase jitter @ 156.25MHz, using a 25MHz crystal (1.875MHz – 20MHz): 0.41ps (typical)
- Full 2.5V supply mode
- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) package

Block Diagram



Pin Assignment

| | | | |
|---------|----|----|----------|
| nc | 1 | 20 | VDDO |
| VDDO | 2 | 19 | Q1 |
| Q0 | 3 | 18 | Q1 |
| Q0 | 4 | 17 | GND |
| MR | 5 | 16 | nc |
| PLL_SEL | 6 | 15 | XTAL_SEL |
| nc | 7 | 14 | REF_CLK |
| VDDA | 8 | 13 | XTAL_IN |
| F_SEL0 | 9 | 12 | XTAL_OUT |
| VDD | 10 | 11 | F_SEL1 |

844002I-01
20-Lead TSSOP
6.5mm x 4.4mm x 0.925mm
package body
G Package
Top View

Table 1. Pin Descriptions

| Number | Name | Type | | Description |
|--------|-------------------------------|--------|----------|---|
| 1, 7 | nc | Unused | | No connect. |
| 2, 20 | V _{DDO} | Power | | Output supply pins. |
| 3, 4 | Q0, Q $\bar{0}$ | Output | | Differential output pair. LVDS interface levels. |
| 5 | MR | Input | Pulldown | Active HIGH Master Reset. When logic HIGH, the internal dividers are reset causing the true outputs Q _x to go low and the inverted outputs \bar{Q}_x to go high. When logic LOW, the internal dividers and the outputs are enabled. LVCMOS/LVTTL interface levels. |
| 6 | $\overline{\text{PLL_SEL}}$ | Input | Pulldown | Selects between the PLL and REF_CLK as input to the dividers. When LOW, selects PLL (PLL Enable). When HIGH, deselects the reference clock (PLL Bypass). LVCMOS/LVTTL interface levels. |
| 8 | V _{DDA} | Power | | Analog supply pin. |
| 9, 11 | FSEL0, F_SEL1 | Input | Pulldown | Frequency select pins. LVCMOS/LVTTL interface levels. |
| 10 | V _{DD} | Power | | Core supply pins. |
| 12, 13 | XTAL_OUT, XTAL_IN | Input | | Parallel resonant crystal interface. XTAL_OUT is the output, XTAL_IN is the input. |
| 14 | REF_CLK | Input | Pulldown | Non-inverting differential clock input. |
| 15 | $\overline{\text{XTAL_SEL}}$ | Input | Pulldown | Selects between crystal or REF_CLK inputs as the PLL Reference source. Selects XTAL inputs when LOW. Selects REF_CLK when HIGH. LVCMOS/LVTTL interface levels. |
| 16 | nc | Unused | | No connect. |
| 17 | GND | Power | | Power supply ground. |
| 18, 19 | \bar{Q}_1, Q_1 | Output | | Differential output pair. LVDS interface levels. |

NOTE: *Pulldown* refers to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

Table 2. Pin Characteristics

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------------|-------------------------|-----------------|---------|---------|---------|------------|
| C _{IN} | Input Capacitance | | | 4 | | pF |
| R _{PULLDOWN} | Input Pulldown Resistor | | | 51 | | k Ω |

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

| Item | Rating |
|---|--------------------------|
| Supply Voltage, V_{DD} | 4.6V |
| Inputs, V_I | -0.5V to $V_{DD} + 0.5V$ |
| Outputs, I_O Continuous Current Surge Current | 10mA 15mA |
| Package Thermal Impedance, θ_{JA} | 73.2°C/W (0 lfp/m) |
| Storage Temperature, T_{STG} | -65°C to 150°C |

DC Electrical Characteristics

Table 3A. Power Supply DC Characteristics, $V_{DD} = V_{DDA} = V_{DDO} = 2.5V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------|-----------------------|-----------------|---------|---------|---------|-------|
| V_{DD} | Core Supply Voltage | | 2.375 | 2.5 | 2.625 | V |
| V_{DDA} | Analog Supply Voltage | | 2.375 | 2.5 | 2.625 | V |
| V_{DDO} | Output Supply Voltage | | 2.375 | 2.5 | 2.625 | V |
| I_{DD} | Power Supply Current | | | | 98 | mA |
| I_{DDA} | Analog Supply Current | | | | 12 | mA |
| I_{DDO} | Output Supply Current | | | | 98 | mA |

Table 3B. LVCMOS/LVTTL DC Characteristics, $V_{DD} = V_{DDA} = V_{DDO} = 2.5V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------|--------------------|--|---------|---------|----------------|---------|
| V_{IH} | Input High Voltage | 2.5V | 1.7 | | $V_{DD} + 0.3$ | V |
| V_{IL} | Input Low Voltage | 2.5V | -0.3 | | 0.7 | V |
| I_{IH} | Input High Current | REF_CLK, MR, FSEL0, FSEL1, PLL_SEL, XTAL_SEL $V_{DD} = V_{IN} = 2.625V$ | | | 150 | μA |
| I_{IL} | Input Low Current | REF_CLK, MR, FSEL0, FSEL1, PLL_SEL, XTAL_SEL $V_{DD} = 2.625V, V_{IN} = 0V$ | -5 | | | μA |

Table 3C. LVDS DC Characteristics, $V_{DD} = V_{DDA} = V_{DDO} = 2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------|-----------------------------|-----------------|---------|---------|---------|-------|
| V_{OD} | Differential Output Voltage | | 240 | | 550 | mV |
| ΔV_{OD} | V_{OD} Magnitude Change | | | 40 | | mV |
| V_{OS} | Offset Voltage | | 0.7 | 1.1 | 1.5 | V |
| ΔV_{OS} | V_{OS} Magnitude Change | | | 50 | | mV |

Table 4. Crystal Characteristics

| Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|------------------------------------|-----------------|-------------|---------|---------|----------|
| Mode of Oscillation | | Fundamental | | | |
| Frequency | | 22.4 | 25 | 27.2 | MHz |
| Equivalent Series Resistance (ESR) | | | | 50 | Ω |
| Shunt Capacitance | | | | 7 | pF |
| Drive Level | | | | 1 | mW |

AC Electrical Characteristics

Table 5. AC Characteristics, $V_{DD} = V_{DDA} = V_{DDO} = 2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------------------|------------------------------------|-------------------------------|---------|---------|---------|-------|
| f_{OUT} | Output Frequency | FSEL[1:0] = 00 | 140 | | 170 | MHz |
| | | FSEL[1:0] = 01 | 112 | | 136 | MHz |
| | | FSEL[1:0] = 10 | 56 | | 68 | MHz |
| $t_{sk(o)}$ | Output Skew; NOTE 1, 2 | | 5 | 20 | ps | |
| $f_{jit}(\emptyset)$ | RMS Phase Jitter, (Random); NOTE 3 | 156.25MHz, (1.875MHz – 20MHz) | | 0.41 | | ps |
| | | 125MHz, (1.875MHz – 20MHz) | | 0.44 | | ps |
| | | 62.5MHz, (1.875MHz – 20MHz) | | 0.47 | | ps |
| t_R / t_F | Output Rise/Fall Time | 20% to 80% | 250 | | 550 | ps |
| odc | Output Duty Cycle | | 48 | | 52 | % |
| t_L | PLL Lock Time | | | | 100 | ms |

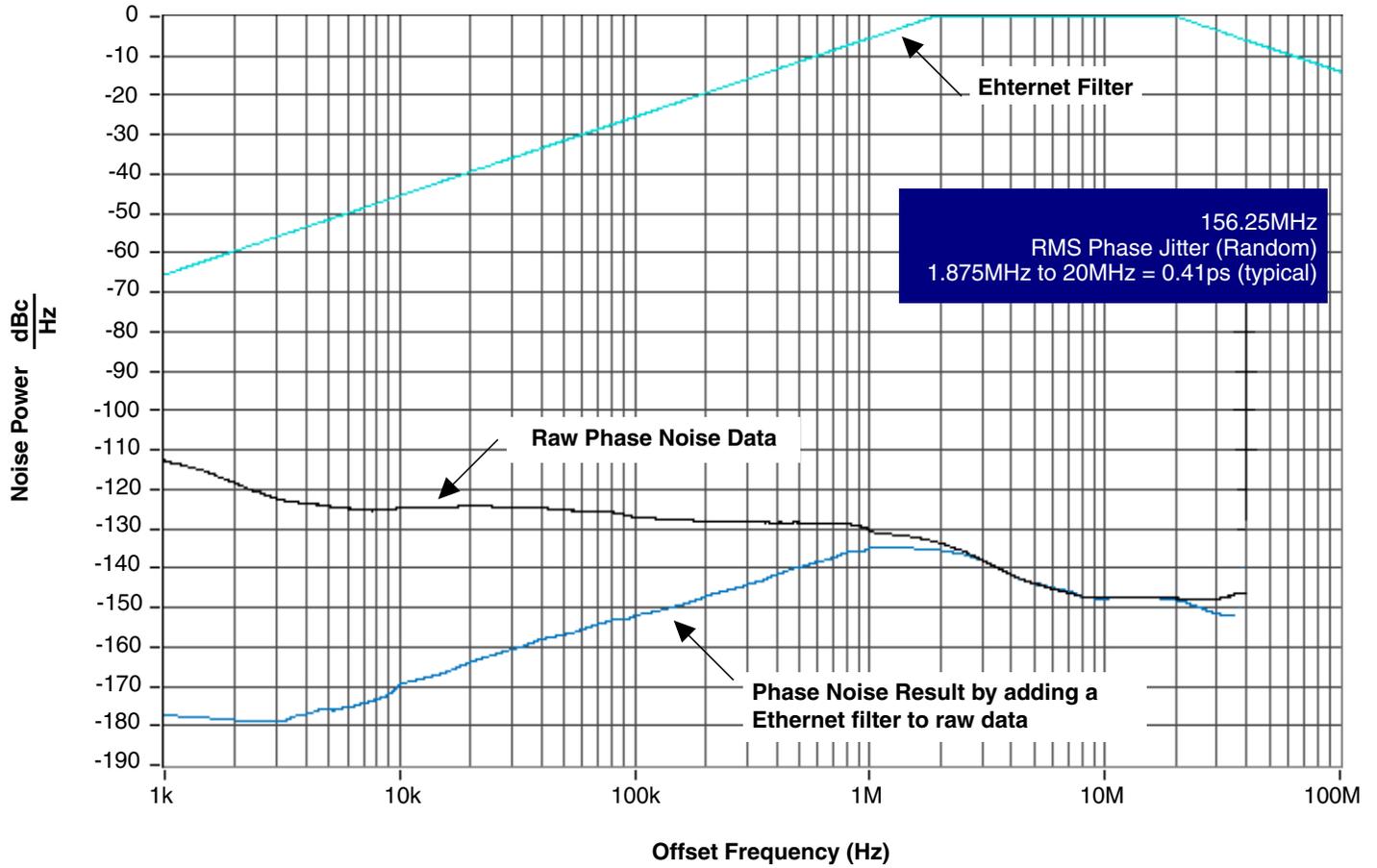
NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when device is mounted in a test socket with maintained transverse airflow greater than 500 lpm. Device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE 1: Defined as skew between outputs at the same supply voltages and with equal load conditions. Measured at $V_{DDO}/2$.

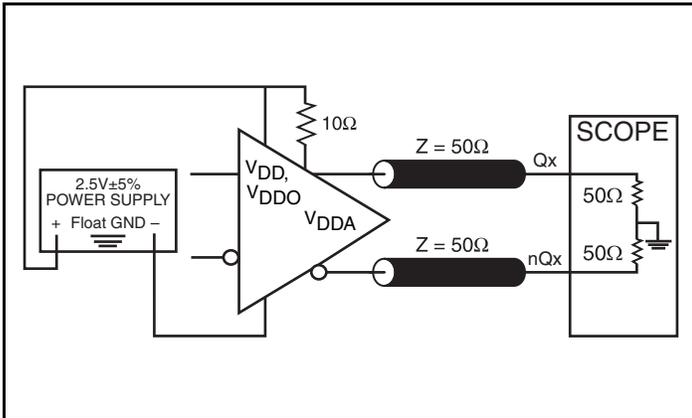
NOTE 2: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 3: Please refer to the Phase Noise Plot.

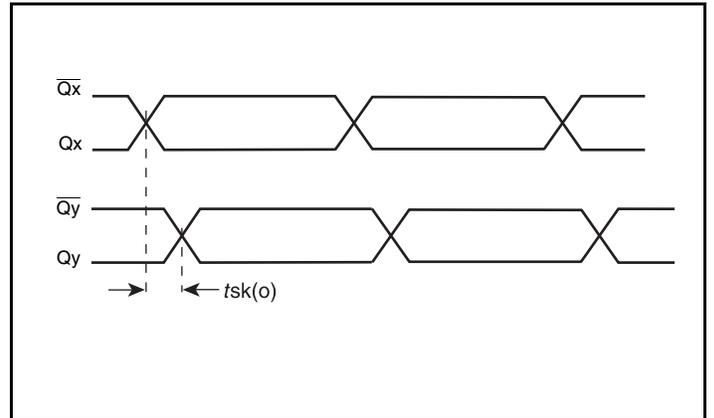
Typical Phase Noise at 156.25MHz



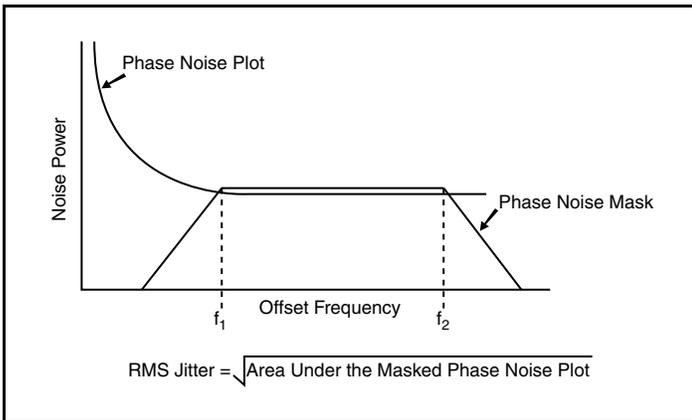
Parameter Measurement Information



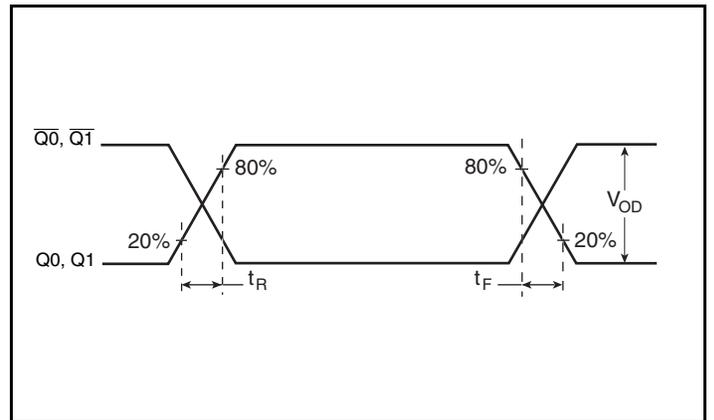
2.5V Output Load AC Test Circuit



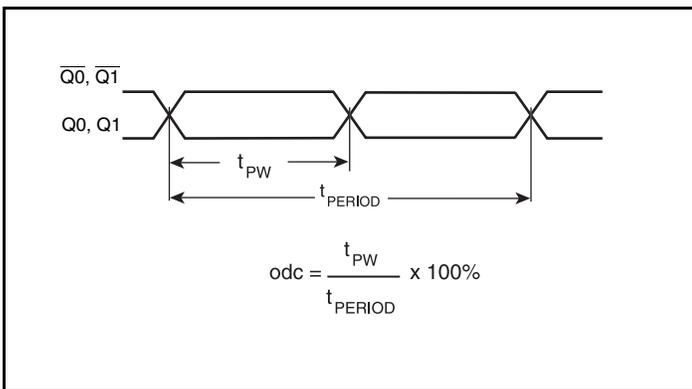
Output Skew



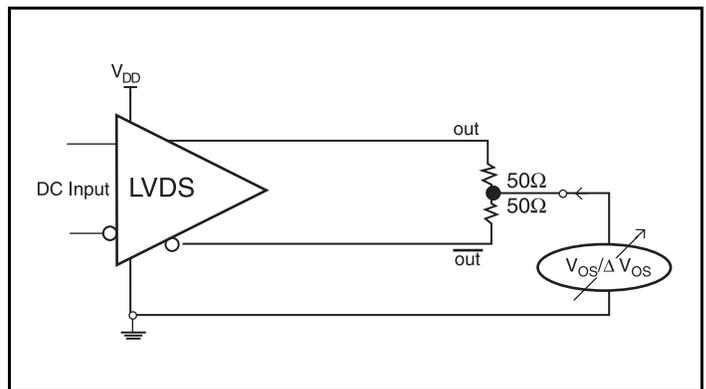
RMS Phase Jitter



Output Rise/Fall Time

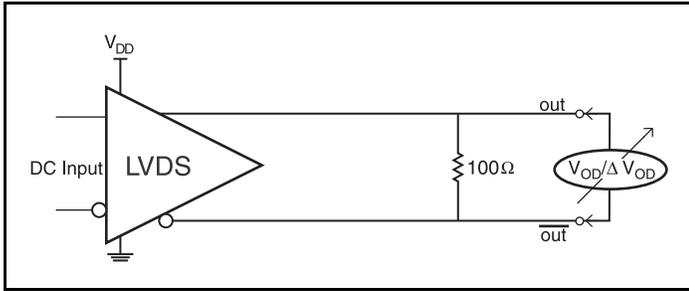


Output Duty Cycle/Pulse Width/Period



Offset Voltage Setup

Parameter Measurement Information, continued



Differential Offset Voltage Setup

Application Information

Power Supply Filtering Technique

As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. The 8440021-01 provides separate power supplies to isolate any high switching noise from the outputs to the internal PLL. V_{DD} , V_{DDA} and V_{DDO} should be individually connected to the power supply plane through vias, and $0.01\mu\text{F}$ bypass capacitors should be used for each pin. *Figure 1* illustrates this for a generic V_{DD} pin and also shows that V_{DDA} requires that an additional 10Ω resistor along with a $10\mu\text{F}$ bypass capacitor be connected to the V_{DDA} pin.

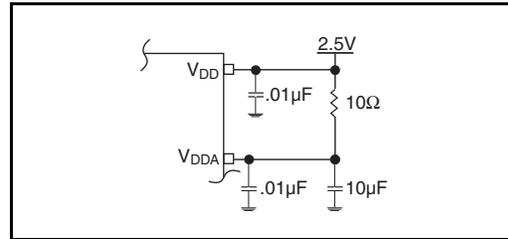


Figure 1. Power Supply Filtering

Recommendations for Unused Input and Output Pins

Inputs:

LVC MOS Control Pins

All control pins have internal pull-downs; additional resistance is not required but can be added for additional protection. A $1\text{k}\Omega$ resistor can be used.

REF_CLK Input

For applications not requiring the use of the reference clock, it can be left floating. Though not required, but for additional protection, a $1\text{k}\Omega$ resistor can be tied from the REF_CLK to ground.

Crystal Inputs

For applications not requiring the use of the crystal oscillator input, both XTAL_IN and XTAL_OUT can be left floating. Though not required, but for additional protection, a $1\text{k}\Omega$ resistor can be tied from XTAL_IN to ground.

Outputs:

LVDS Outputs

All unused LVDS output pairs can be either left floating or terminated with 100Ω across. If they are left floating, we recommend that there is no trace attached.

Crystal Input Interface

The 844002I-01 has been characterized with 18pF parallel resonant crystals. The capacitor values shown in *Figure 2* below

were determined using a 25MHz, 18pF parallel resonant crystal and were chosen to minimize the ppm error.

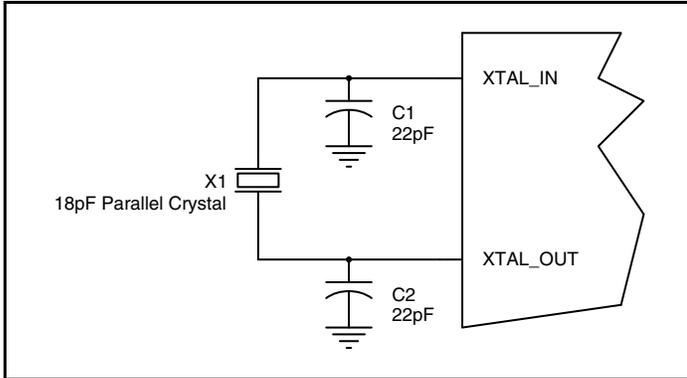


Figure 2. Crystal Input Interface

LVC MOS to XTAL Interface

The XTAL_IN input can accept a single-ended LVC MOS signal through an AC coupling capacitor. A general interface diagram is shown in *Figure 3*. The XTAL_OUT pin can be left floating. The input edge rate can be as slow as 10ns. For LVC MOS inputs, it is recommended that the amplitude be reduced from full swing to half swing in order to prevent signal interference with the power rail and to reduce noise. This configuration requires that the output

impedance of the driver (R_o) plus the series resistance (R_s) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This can be done in one of two ways. First, R_1 and R_2 in parallel should equal the transmission line impedance. For most 50Ω applications, R_1 and R_2 can be 100Ω. This can also be accomplished by removing R_1 and making R_2 50Ω.

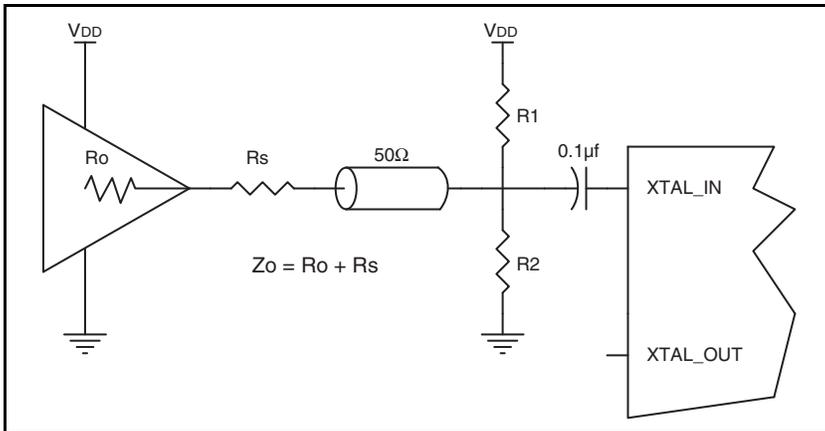


Figure 3. General Diagram for LVC MOS Driver to XTAL Input Interface

2.5V LVDS Driver Termination

Figure 4 shows a typical termination for LVDS driver in characteristic impedance of 100Ω differential (50Ω single) transmission line

environment. For buffer with multiple LVDS driver, it is recommended to terminate the unused outputs.

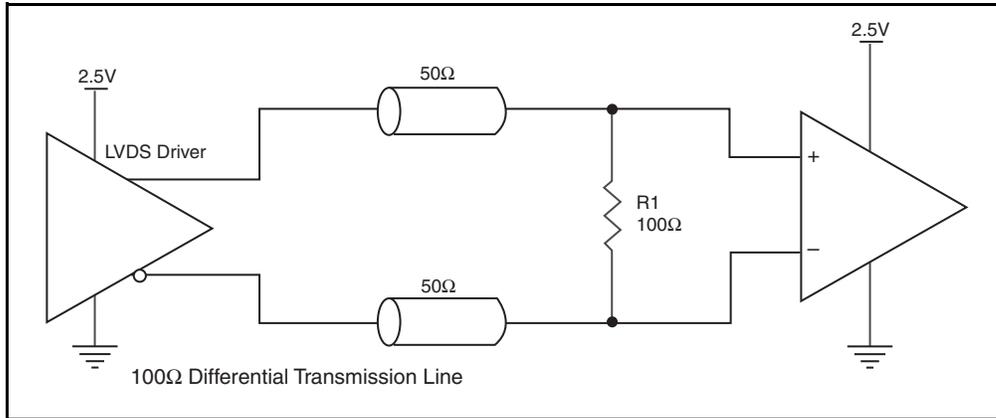


Figure 4. Typical LVDS Driver Termination

Power Considerations

This section provides information on power dissipation and junction temperature for the 844002I-01. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the ICS44002I-01 is the sum of the core power plus the analog power plus the power dissipated in the load(s). The following is the power dissipation for $V_{DD} = 2.5V + 5\% = 2.625V$, which gives worst case results.

- Power (core)_{MAX} = $V_{DD_MAX} * (I_{DD_MAX} + I_{DDA_MAX}) = 2.625V * (98mA + 12mA) = \mathbf{288.75mW}$
- Power (outputs)_{MAX} = $V_{DDO_MAX} * I_{DDO_MAX} = 2.625V * 98mA = \mathbf{257.25mW}$

Total Power_{MAX} = 288.75mW + 257.25mW = **546mW**

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad and directly affects the reliability of the device. The maximum recommended junction temperature for HiPerClockS devices is 125°C.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_total + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming a moderate air flow of 200 linear feet per minute and a multi-layer board, the appropriate value is 66.6°C/W per Table 6 below.

Therefore, T_j for an ambient temperature of 85°C with all outputs switching is:

$$85^\circ\text{C} + 0.546\text{W} * 66.6^\circ\text{C}/\text{W} = 121.4^\circ\text{C}. \text{ This is below the limit of } 125^\circ\text{C}.$$

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (single layer or multi-layer).

Table 6. Thermal Resistance θ_{JA} for 20 Lead TSSOP, Forced Convection

| Linear Feet per Minute | θ_{JA} by Velocity | | |
|--|---------------------------|----------|----------|
| | 0 | 200 | 500 |
| Single-Layer PCB, JEDEC Standard Test Boards | 114.5°C/W | 98.0°C/W | 88.0°C/W |
| Multi-Layer PCB, JEDEC Standard Test Boards | 73.2°C/W | 66.6°C/W | 63.5°C/W |

Reliability Information

Table 7. θ_{JA} vs. Air Flow Table for a 20 Lead TSSOP

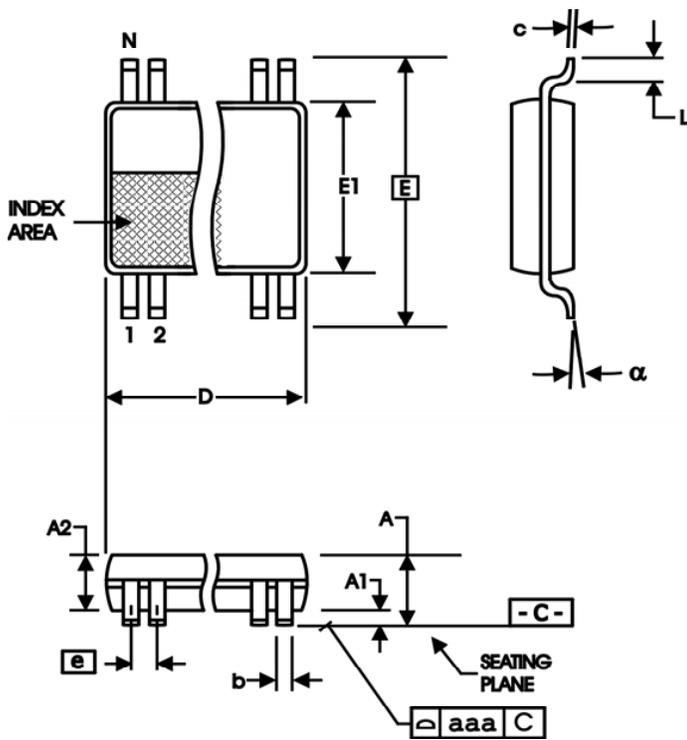
| θ_{JA} by Velocity | | | |
|--|-----------|----------|----------|
| Linear Feet per Minute | 0 | 200 | 500 |
| Single-Layer PCB, JEDEC Standard Test Boards | 114.5°C/W | 98.0°C/W | 88.0°C/W |
| Multi-Layer PCB, JEDEC Standard Test Boards | 73.2°C/W | 66.6°C/W | 63.5°C/W |

Transistor Count

The transistor count for 844002I-01 is: 2914

Package Outline and Package Dimensions

Package Outline - G Suffix for 20 Lead TSSOP



| All Dimensions in Millimeters | | |
|-------------------------------|------------|---------|
| Symbol | Minimum | Maximum |
| b | 0.19 | 0.30 |
| c | 0.09 | 0.20 |
| D | 6.40 | 6.60 |
| E | 6.40 Basic | |
| E1 | 4.30 | 4.50 |
| e | 0.65 Basic | |
| L | 0.45 | 0.75 |
| α | 0° | 8° |
| aaa | | 0.10 |

Reference Document: JEDEC Publication 95, MO-153

Table 8. Package Dimensions

| All Dimensions in Millimeters | | |
|-------------------------------|---------|---------|
| Symbol | Minimum | Maximum |
| N | 20 | |
| A | | 1.20 |
| A1 | 0.05 | 0.15 |
| A2 | 0.80 | 1.05 |

Ordering Information

Table 9. Ordering Information

| Part/Order Number | Marking | Package | Shipping Packaging | Temperature |
|-------------------|--------------|---------------------------|--------------------|---------------|
| 844002AGI-01LF | ICS4002AI01L | "Lead-Free" 20 Lead TSSOP | Tube | -40°C to 85°C |
| 844002AGI-01LFT | ICS4002AI01L | "Lead-Free" 20 Lead TSSOP | Tape & Reel | -40°C to 85°C |

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

Revision History Sheet

| Rev | Table | Page | Description of Change | Date |
|-----|-----------|------|--|----------|
| C | T1 T3B | 1 | Pin Assignment - correct pin 16 from V_{DD} to nc. | 9/28/07 |
| | | 2 | Pin Description Table - deleted pin 16 from V_{DD} row. Added Pin 16 row, "nc". | |
| | | 3 | LVC MOS DC Characteristics Table - corrected I_{IL} from -150 μ A min. to -5 μ A min. | |
| | | 7 | Parameter Measurement Information - corrected Output Rise/Fall Time diagram. | |
| | | 10 | Power Considerations - updated calculations. | |
| D | T5 | 4 | AC Characteristics Table - added PLL Lock Time. | 10/20/08 |
| | | 6 | Parameter Measurement Information - deleted 3.3V Output Load AC Test Circuit and added RMS Phase Jitter diagram. | |
| D | T9 | 12 | Ordering Information - removed leaded devices. Updated data sheet format. | 6/9/15 |
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Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu,
Koto-ku, Tokyo 135-0061, Japan
www.renesas.com

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